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Coaxial see-through inspection system

Abstract

Aspects of the present disclosure provide an inspection system, which can include an image module and processing circuitry. The imaging module can image a wafer with a first light beam and a second light beam. The first light beam can be coaxially aligned with the second light beam, and image a first pattern located on a front side of a wafer to form a first image. The second light beam can image a second pattern located below the first pattern to form a second image via quantum tunneling imaging or infrared transmission imaging. The second light beam can have power sufficient to pass through at least a portion of a thickness of the wafer and reach the second pattern. The processing circuitry can perform image analysis on the first image and the second image to calculate an overlay value of the first and second patterns and/or defects of the wafer.

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Background/Summary

INCORPORATION BY REFERENCE (1) This present disclosure claims the benefit of U.S. Provisional Application No. 63/066,779, “Method for Producing Overlay Results with Absolute Reference for Semiconductor Manufacturing” filed on Aug. 17, 2020, which is incorporated herein by reference in its entirety.

FIELD OF THE PRESENT DISCLOSURE

(1) The present disclosure relates generally to methods of fabricating semiconductor devices and specifically to overlay error.

BACKGROUND

(2) Semiconductor fabrication involves multiple varied steps and processes. One typical fabrication process is known as photolithography (also called microlithography). Photolithography uses radiation, such as ultraviolet or visible light, to generate fine patterns in a semiconductor device design. Many types of semiconductor devices, such as diodes, transistors, and integrated circuits, can be constructed using semiconductor fabrication techniques including photolithography, etching, film deposition, surface cleaning, metallization, and so forth.

SUMMARY

(3) Aspects of the present disclosure provide an inspection system. For example, the inspection system can include an imaging module and processing circuitry. The imaging module can image a wafer with a first light beam and a second light beam that is coaxially aligned with the first light beam. The first light beam can image a first pattern located on a front side of a wafer to form a first image. The second light beam can image a second pattern located below the first pattern to form a second image, and have power sufficient to pass through at least a portion of a thickness of the

wafer and reach the second pattern. The processing circuitry can perform image analysis on the first image and the second image to calculate at least one of an overlay value of the first pattern and the second pattern and inspect defects of the wafer. In an embodiment, the second pattern can include a radioactive or fluorescent material. In another embodiment, the second pattern can include at least one of a point, a line, a corner, a box, a triangle, a number and a mark.

(4) In an embodiment, the second pattern can be incorporated in a reference plate located below the wafer. For example, the reference plate can be placed on or adhered to a back side of the wafer. As another example, the reference plate can be incorporated in a substrate holder of a photolithography scanner or stepper. In another embodiment, the second pattern can be projected on a surface of the wafer.

(5) In an embodiment, the second pattern can be formed on a back side of the wafer, and the second light beam can have the power sufficient to pass through an entire thickness of the wafer and reach the second pattern. In another embodiment, the second pattern can be embedded within the wafer.

(6) In an embodiment, the second wavelength can have a second wavelength longer than a first wavelength of the first light beam. 10. For example, the first wavelength can be 50-400 nanometers, and the second wavelength can be 1-10 micrometers. As another example, the first wavelength can be 266 nanometers, and the second wavelength can be 3.6 or 3.7 micrometers.

(7) In an embodiment, the inspection system can further include an ultraviolet (UV) light source configured to generate the first light beam, and an infrared (IR) light source configured to generate the second light beam. For example, the second pattern can be imaged via quantum tunneling imaging or IR transmission imaging.

(8) In an embodiment, the second pattern can be coaxially aligned with the wafer.

(9) In an embodiment, the processing circuitry can perform the image analysis by identifying coordinate locations of the first pattern relative to the second pattern as the overlay value.

(10) As can be appreciated, as fabrication progresses on a given wafer, depending on a given device being created, there can be many different materials and layers. Thus each wafer at each process stage can have a different profile. This means a different wavelength may be needed to pass through the wafer.

(11) Of course, the order of discussion of the different steps as described herein has been presented for clarity sake. In general, these steps can be performed in any suitable order. Additionally, although each of the different features, techniques, configurations, etc. herein may be discussed in different places of this disclosure, it is intended that each of the concepts can be executed independently of each other or in combination with each other. Accordingly, the present disclosure can be embodied and viewed in many different ways.

(12) Note that this summary section does not specify every embodiment and/or incrementally novel aspect of the present disclosure or claimed disclosure. Instead, this summary only provides a preliminary discussion of different embodiments and corresponding points of novelty over conventional techniques. For additional details and/or possible perspectives of the present disclosure and embodiments, the reader is directed to the Detailed Description section and corresponding figures of the present disclosure as further discussed below.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

- (1) Various embodiments of this disclosure that are proposed as examples will be described in detail with reference to the following figures, wherein like numerals reference like elements, and wherein:
- (2) FIG. 1A shows an industrial problem of overlay;
- (3) FIG. 1B shows overlay alleviation using an exemplary reference pattern in accordance with

some embodiments of the present disclosure;

(4) FIG. 2 is a functional block diagram of an exemplary imaging system in accordance with some embodiments of the present disclosure;

(5) FIG. 3 is an enlarged view of a portion of coaxially aligned light beams generated by the exemplary imaging system of FIG. 2;

(6) FIG. 4A shows an enlarged top view of superimposed images of a portion of a wafer captured by the first and second image capturing devices of the exemplary imaging system of FIG. 2 in accordance with some embodiments of the present disclosure

(7) FIG. 4B demonstrates exemplary image analysis for overlay calculation using an absolute, independent reference pattern in accordance with some embodiments of the present disclosure;

(8) FIG. 5 is a flow chart illustrating an exemplary imaging method in accordance with some embodiments of the present disclosure; and

(9) FIG. 6 is a functional block diagram of an exemplary inspection system in accordance with some embodiments of the present disclosure.

DETAILED DESCRIPTION

(10) In accordance with the present disclosure, an imaging method is provided, which uses an absolute, independent reference pattern as an alignment mark for feature patterns to be aligned with, instead of being aligned with a previous pattern. The feature patterns can be formed on a front side of a wafer, and the reference pattern is independent of the front side of the wafer. For example, the reference pattern can be formed within or below the wafer. A first light beam (e.g., an ultraviolet (UV) light beam) of a first wavelength can be used to image the feature patterns formed on the first side of the wafer, and a second light beam (e.g., an infrared (IR) light beam) of a second wavelength can be used to image the reference pattern formed within or below the wafer. In an embodiment, the second light beam can be coaxially aligned with the first light beam. As the reference pattern is formed within or below the wafer, the second light beam has to “see through” a portion of the thickness or the entire thickness of the wafer in order to image the reference pattern. For example, the second light beam can have power or intensity sufficient to pass through a portion of the thickness or the entire thickness of the wafer, depending on whether the reference pattern is formed within or below the wafer, to capture an image of the reference pattern using quantum tunneling imaging, IR transmission imaging or the like. Therefore, UV images of the feature patterns and IR images of the reference pattern can be captured in the same light axis and superimposed on each other. Image analysis can then be performed for exposure, inspection, alignment or other processing. Although the UV and IR images are captured coaxially, transmission to an image detector may or may not be coaxial. For example, the coaxially captured images may be optically separated and transmitted to separate image detectors as discussed below.

(11) The following disclosure provides many different embodiments, or examples, for implementing different features of the provided subject matter. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed. Further, spatially relative terms, such as “top,” “bottom,” “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures.

The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

(12) The order of discussion of the different steps as described herein has been presented for clarity sake. In general, these steps can be performed in any suitable order. Additionally, although each of the different features, techniques, configurations, etc. herein may be discussed in different places of this disclosure, it is intended that each of the concepts can be executed independently of each other or in combination with each other. Accordingly, the present disclosure can be embodied and viewed in many different ways.

(13) Microfabrication involves forming and processing multiple films and layers on a wafer. This can include dozens or more films stacked on a wafer. Patterns applied to the wafer for various films and layers need to be aligned to previously-formed patterns. Conventionally, such alignment is realized by using part of the wafer to form alignment marks and scribe lines. However, the present inventors recognized that the various film deposition, etching, and treatment techniques at times cover the alignment marks and even completely remove the alignment marks. With alignment marks at times covered or missing, there can be errors applying subsequent patterns on the wafer. The term overlay or overlay error refers to the difference between placement of given pattern relative to a previously-placed pattern. With alignment marks routinely destroyed, overlay error can accumulate with additional layers, which can cause poor performance and device error.

(14) FIG. 1A illustrates an industrial problem of overlay. Each arrow herein has a starting point (e.g., **111A**, **111B**, **121A** and **131A**), which corresponds to a position of a preceding pattern, and an endpoint or arrowhead (e.g., **111A'**, **111N'**, **121N'**), which corresponds to a position of a subsequent pattern. As a result, each arrow represents an overlay value or overlay error when the subsequent pattern is formed over or side by side with the corresponding preceding pattern. In a process **110A**, for example, there is no grid or reference plate when placing an initial pattern. Thus, a starting point **111A** of a first arrow is likely to be misaligned, that is, the initial pattern can have a placement error, for example relative to the wafer edge. Then subsequent patterns try to align based on the corresponding last pattern. As illustrated in FIG. 1A, a starting point (e.g., **111B**) of a subsequent arrow overlaps with an arrowhead (e.g., **111A'**) of a corresponding last or preceding arrow. In some embodiments, deterioration of alignment marks can cause alignment error for subsequent patterns placed by using such deteriorated alignment marks. Note that even in a theoretically perfect system, walkout can still occur. For example, if a system pattern placement tolerance is ± 4 nm and each level references a previous level. Take a reference level to be 0 error. A first layer then could be $+4$ nm off. A second layer alignment to the first layer could be $+4$ nm off, meaning the second layer is now $+8$ nm off the reference level. There are also process factors that induce or relieve stress throughout fabrication that can induce walkout/alignment shift even with pristine alignment marks visible that can add to accumulated error.

(15) Further, alignment marks may be destroyed at a step **S120** in a manufacturing process, and placement again happens without a reference mark. Deterioration of alignment marks can cause accumulation of alignment error with subsequent processing. Similar to the starting point **111A**, a starting point **121A** of a new arrow is likely to be misaligned. In the example of FIG. 1A, the starting point **121A** deviates from an arrowhead **111N'**. The process proceeds by aligning subsequent patterns based on the corresponding last pattern until alignment marks are destroyed again at a step **S130**. Similarly, placement happens without a reference mark, and a starting point **131A** deviates from an arrowhead **121N'**. As can be seen in FIG. 1A, as layers increase, the overlay error can accumulate leading to poor manufacturing yield, device error, etc. Note that the process **110A** is a non-limiting example. Other processes (e.g., **110B** and **110C**) may have different overlay values (different arrows) and/or different steps.

(16) FIG. 1B shows overlay alleviation using an exemplary reference pattern in accordance with some embodiments of the present disclosure. With techniques herein, all patterns (e.g., a pattern having a starting point **141A**) placed on a front side (or working side) **191** of a wafer **190** are based

on a same reference pattern **102**. In an embodiment, the reference pattern **102** can be located below the front side **191** of the wafer **190**. For example, the reference pattern **102** can be formed on a back side **192** of the wafer **190** or incorporated in the wafer **190**. As another example, the reference pattern **102** can be incorporated in a reference plate (not shown in FIG. **1B**), and the reference plate can be positioned below the wafer **190**, placed on or adhered to the back side **192** of the wafer **190**, or incorporated in a substrate holder of a photolithography scanner or stepper (not shown in FIG. **1B**) that is used to hold the wafer **190**. In other words, the reference pattern **102** is not affected by lithographic processes, such as etching, deposition, chemical mechanical polishing and the like, which are performed on the front side **191** of the wafer **190** in order to form patterns. Therefore, the reference pattern **102** is independent of the front side **191** of the wafer **190**, and will be intact during the lithographic processing of the wafer **190**. Accordingly, the reference pattern **102** can be used and considered absolute, or rather, independent of any patterns formed on the front side **191** of the wafer **190**, and will not be changed from various deposition and etch steps performed on the wafer **190**. In an embodiment, the reference pattern **102** can be compared to the wafer **190** when placing a new pattern. For an initial pattern, this means that the pattern can be fitted to the reference pattern **102**. For subsequent patterns, this means that one or more patterns can still be compared to the reference pattern **102** to calculate overlay correction to return to a same alignment.

(17) For example, in a process **140** the reference pattern **102** can be used to align an initial pattern on the front side **191** of the wafer **190**. In one embodiment, the reference pattern **102** can be provided in a fixed position relative to the wafer surface such as by embedding the reference pattern **102** within the wafer **190** or providing the reference pattern **102** fixed to a back side **192** of the wafer **190**. Consequently, a starting point **141A** of a first arrow is aligned to the reference pattern **102**, whose position is demonstrated as a reference line **150**. Subsequent patterns are also aligned using the fixed absolute, independent reference pattern **102**. A new photoresist layer may be formed for each subsequent pattern, but no alignment marks need to be formed and/or destroyed on the wafer **190** due to the reference pattern **102**. As a result, arrows center around the reference line **150**, meaning that the subsequent patterns are aligned to the reference pattern **102**. Alignment may occur, for example, by moving a mask of the pattern image or moving the wafer **190** relative to the mask. Overlay error is therefore unlikely to accumulate as more and more layers are formed.

(18) FIG. **2** is a functional block diagram of an exemplary imaging system **200** in accordance with some embodiments of the present disclosure. For example, the exemplary imaging system **200** can be implemented in a scanner or a stepper of a lithography system. As another example, the exemplary imaging system **200** can be implemented in a resist coating tool, e.g., CLEAN TRACK™ ACT™12 manufactured by Tokyo Electron Ltd, the resists coating tool containing multiple mask-specific modules such as advance softbake oven units, edge-bead removal modules, and cleaning systems. The exemplary imaging system **200** can coaxially align two light beams of different wavelengths, focus the two coaxially aligned light beams onto a first pattern located on a front side of a substrate (e.g., a wafer) and a second pattern located below the first pattern, respectively, and capture images of the first and second patterns. For example, the exemplary imaging system **200** can include a first light source **210**, a second light source **220**, an alignment module **230**, a coaxial module **240**, a first image capturing device **250** and a second image capturing device **260**. The first image capturing device **250** and the second image capturing device **260** can be referred to as an image capturing module collectively.

(19) In an embodiment, the first light source **210** can be configured to generate a first incident light beam of a first wavelength. For example, the first light source **210** can be a UV light source that generates a first incident light beam of 50-400 nanometers, e.g., 266 nanometers (shown in FIG. **2** as UV.sub.incident). As another example, the first light source **210** can be an Optowaves (Optowares Inc., Massachusetts, USA) solid state lasers, such as pumped nanosecond laser for surface imaging.

(20) In an embodiment, the second light source **220** can be configured to generate a second incident

light beam of a second wavelength. According to some aspects of the present disclosure, as an absolute, independent reference pattern shall be located below a pattern that is to be formed on a front side of a wafer and the second incident light beam is used to image the reference pattern, the second incident light beam has to see through at least a portion of a thickness or even the entire thickness of the wafer, such as a wafer **290**.

(21) For example, the second incident light beam has power or intensity sufficient to pass through the entire thickness (e.g., 750 micrometers) of the wafer **290** to capture an image of the reference pattern using quantum tunneling imaging, IR transmission imaging or the like. As another example, the second light source **220** can be an IR light source that generates a second incident light beam of 1-10 micrometers, e.g., 3.6 or 3.7 micrometer (shown in FIG. 2 as IR.sub.incident). In an embodiment, the second light source **220** can be IR tunable quantum cascade lasers, which can be obtained from Pranalytica, Inc. (California, USA). According to evanescent wave theory, a light beam impinging at a surface (e.g., a front side **391** of the wafer **290**, as shown in FIG. 3) between two different media (e.g., the wafer **290** and air or liquid in immersion lithography where the coaxial module **240** is located) will have its intensity decayed exponentially perpendicular to the surface. The penetration depth over which the intensity drops to $1/e$ (approximately 37%) depends on, among other things, the wavelength of the light beam. Typical penetration depth can be a fraction of the wavelength of the light beam, e.g., $1/5$ of the wavelength, depending on the incident angle of the light beam to the surface. As the second wavelength of the second incident light beam IR.sub.incident is much longer than the first wavelength of the first incident light beam UV.sub.incident, the second incident light beam IR.sub.incident, with power well controlled, can be capable of passing through the entire thickness of the wafer **290**.

(22) In an embodiment, the relative position of the first (UV) light source **210** and the second (IR) light source **220** can be calibrated periodically, which is also referred to as relative position of red and blue calibration. For example, the relative position of the first light source **210** and the second light source **220** can be kept within a sensor dynamic range which is a few decades and as such quite forgiving. Normalization, however, can be done with a stage artifact of known relative transmission being imaged as needed. For example, once a day so that any relative intensity normalization can be conducted easily. Relative position or TIS tool induced shift calibrations are common to metrology stations. Relative position is recalibrated against the grid plate in real time as measurements are made. Accordingly, the exemplary imaging system **200** can always have a real time absolute reference. Digital image capture and regression can be used.

(23) In an embodiment, the alignment module **230** can be configured to coaxially align the second incident light beam IR.sub.incident with the first incident light beam UV.sub.incident. For example, the alignment module **230** can include a first light beam splitter that splits the first incident light beam UV.sub.incident into two parts, one of which can be transmitted and the other of which can be reflected. In an embodiment, the first light beam splitter can be a prism. In another embodiment, the first light beam splitter can be a transparent plate, such as a sheet of glass or plastic, coated on one side thereof with a partially transparent thin film of metal, such as aluminum, which allows one part of the first incident light beam UV.sub.incident to be transmitted and the other part to be reflected. In the exemplary imaging system **200**, the first light source **210** and the first light beam splitter can be arranged such that the first incident light beam UV.sub.incident is incident at a 45-degree angle to the first light beam splitter.

(24) For example, the alignment module **230** can further include a second light beam splitter that splits the second incident light beam IR.sub.incident into two parts, one of which can be reflected and the other of which can be transmitted. For example, the second light beam splitter can be a prism. As another example, the second light beam splitter can be a sheet of glass or plastic coated on one side thereof with a thin film of aluminum, which allows one part of the second incident light beam IR.sub.incident to be reflected and the other part to be transmitted. In the exemplary imaging system **200**, the second light source **220** and the second light beam splitter can be arranged such

that the second incident light beam IR.sub.incident is incident at a 45-degree angle to the second light beam splitter.

(25) For example, the alignment module **230** can further include a third beam splitter that allows light beams of different wavelengths to be either reflected or transmitted. For example, the third beam splitter can be a transparent plate coated on one side thereof with a dichroic material that allows the first incident light beam UV.sub.incident of the first wavelength that is transmitted from the first light beam splitter to be reflected, and the second incident light beam IR.sub.incident of the second wavelength that is transmitted from the second light beam splitter to be transmitted. In an embodiment, the third beam splitter is designed and located such that the transmitted second incident light beam IR.sub.incident is coaxially aligned with the reflected first incident light beam UV.sub.incident and the transmitted second incident light beam IR.sub.incident and the reflected first incident light beam UV.sub.incident can travel to the wafer **290** along the same light path.

(26) In an embodiment, the coaxial module **240** can be configured to focus the first incident light beam UV.sub.incident reflected from the third beam splitter onto a first pattern **301** (shown in FIG. 3) located on a front side **391** of the wafer **290**, and focus the second incident light beam IR.sub.incident transmitted from the third beam splitter onto a second pattern **302** (or a reference pattern) located below the first pattern **301**. For example, the coaxial module **240** can be designed and configured to adjust the tolerances of the placement (i.e., depth of focus (DOF)) of the first pattern **301** and the second pattern **302**. For example, a level sensor can be used to track the top of the first pattern **301** and subtract the height of the first pattern **301** by the height of the wafer **290** to auto-adjust the DOFs of the coaxially aligned first incident light beam UV.sub.incident and second incident light beam IR.sub.incident simultaneously. With deep UV (DUV) light, photoresist damage can be negligible. A 250-micrometer field of view (FOV) herein corresponds with about 60 nanometers per pixel in the case of 4K resolution. It is sufficient for resolution of 0.1-nanometer registration error measurement. Having sufficient power or intensity of light source can mitigate any shadowing of metal layers. While FIG. 3 shows imaging of a physical pattern formed in the wafer **290**, images of a pattern to be formed (i.e., prior to exposure to activating light) may be realized by light having a wavelength that does not activate photoresist in the wafer, for example.

(27) In an embodiment, the coaxial module **240** can include 2-12 individual optical elements, e.g., 6 optical elements. Each of the optical elements can include sapphire, AlN, MgF, CaF, BaF, LiF, Ge, Si, etc.

(28) The first incident light beam UV.sub.incident can be reflected by the first pattern **301** to form a first reflection light beam UV.sub.reflection. The first reflection light beam UV.sub.reflection can be reflected by the third beam splitter and the first light beam splitter sequentially and captured by the first image capturing device **250**, and the first image capturing device **250** can form a corresponding first image of the first pattern **301**. For example, the first image capturing device **250** can be DataRay camera. The second incident light beam IR.sub.incident can be reflected by the second pattern **302** to form a second reflection light beam IR.sub.reflection. The second reflection light beam IR.sub.reflection can be transmitted by the third beam splitter and the second light beam splitter sequentially and captured by the second image capturing device **260**, and the second image capturing device **260** can form a corresponding second image of the second pattern **302**. For example, the second image capturing device **260** can be a high speed, high definition middle wavelength IR (MWIR) camera, e.g., FLIR X8500 MWIR. In an embodiment, image analysis can be performed on the first image and the second image to calculate an overlay value to determine the placement of the first pattern **301**. For example, the image analysis can be accomplished by superimposing the first image of the first pattern **301** and the second image of the second pattern **302** on each other, and identifying coordinate locations of the first pattern **301** relative to the second pattern **302**. In some embodiments, the image analysis can be performed in real time so that the placement of the first pattern **301** can be adjusted in real time.

(29) In an embodiment, the alignment module **230** can further include a first lens set and a second

lens set. For example, the first lens set can include reflective and/or refractive optics that collimate the first incident light beam UV.sub.incident generated by the first light source **210** and direct the collimated first incident light beam UV.sub.incident to the first light beam splitter. As another example, the second lens set can also include reflective and/or refractive optics that collimate the second incident light beam IR.sub.incident generated by the second light source **220** and direct the collimated second incident light beam IR.sub.incident to the second light beam splitter.

(30) In an embodiment, the exemplary imaging system **200** can further include a third lens set **270** and a fourth lens set **280**. For example, the third lens set **270** can include reflective and/or refractive optics that focus the first reflection light beam UV.sub.reflection onto the first image capturing device **250**. As another example, the fourth lens set **280** can also include reflective and/or refractive optics that focus the second reflection light beam IR.sub.reflection onto the second image capturing device **260**.

(31) In an embodiment, the exemplary imaging system **200** can further include optics that can capture diffracted light beams outside of the coaxial module **240** and direct them to the first image capturing device **250** and the second image capturing device **260**.

(32) In the exemplary embodiment shown in FIG. 3, the first pattern **301** can be included in a photomask (not shown) that is located on the front side **391** of the wafer **290**. In an embodiment, the photomask can be placed in direct contact with the wafer **290** in a contact printing system. In another embodiment, the photomask can be placed away from the wafer **290** in a proximity printing system or in a projection printing system.

(33) In the exemplary embodiment shown in FIG. 3, the second pattern **302** is located on a back side **392** of the wafer **290**, and the second incident light beam IR.sub.incident has power sufficient to pass through the entire thickness of the wafer **290** to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. In an embodiment, the second pattern **302** can be formed on a reference plate **310**. For example, the reference plate **310** can be a grid plate with 20 micrometers by 20 micrometers squares, nearly perfectly aligned, and the second pattern **302** can be a corner point of at least one of the squares. As another example, the reference plate **310** can include at least one of a point, a line, a corner, a box, a number, a mark, or any other pattern that is suitable for alignment purpose, and the second pattern **302** can be one of these. In an embodiment, the reference plate **310** can be adhered to the back side **392** of the wafer **290**. Accordingly, the reference plate **310** and the wafer **290** can function as one module. In another embodiment, the reference plate **310** can be incorporated in a substrate holder **320** of a photolithography scanner or stepper. Although each time a given wafer may be placed on the substrate holder **320** in a different position or orientation as compared to a previous placement, this does not matter. For a given new pattern to be placed or exposed, the wafer can be imaged with the reference plate **310**, e.g., the grid plate. The reference plate **310** can then provide a relatively reference point for identifying vectors to two or more points, from which vector analysis can be used to calculate an overlay correction adjustment in a next exposure. For example, when the wafer **290**, if having no pattern yet, is placed over the reference plate **310**, the wafer **290** will be coarsely pre-aligned to the reference plate **310**. As another example, when the wafer **290**, if having an existing pattern already, is placed over the reference plate **310**, the existing pattern and the reference plate **310** can be co-axially aligned. In a conventional lithography process, measurement errors caused by wafer back side scratches, back side dust and/or substrate distortion due to heat, may impact overlay, but conventional overlay systems are often blind to these problems. Techniques herein include an independent reference plate and high spatial resolution to overcome these problems.



(34) In an embodiment, the second pattern **302** can be formed on the back side **392** of the wafer **290**, and the second incident light beam IR.sub.incident also has power sufficient to pass through the entire thickness of the wafer **290** to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. Other techniques can include





embedding the second pattern **302** (e.g., grid lines) in the wafer **290** such as using a radioactive or fluorescent material.

(35) In an embodiment, the second pattern **302** can be formed on the front side **291** of the wafer **290**, and then a layer of silicon and/or silicon oxide is deposited thereon. For example, the layer of silicon and/or silicon oxide can have a thickness of 1-5 micrometers so that the second pattern **302** is effectively “embedded” in the wafer **290** and patterns can be formed on the layer of silicon and/or silicon oxide. Accordingly, the second incident light beam IR.sub.incident has to have power sufficient to pass through the layer of silicon and/or silicon oxide in order to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. As another example, the second pattern **302** can be formed on the back side **292** of the wafer **290** before a protection layer, such as silicon or silicon oxide formed on the back side **292** of the wafer **290**. Consequently, the second pattern **302** can also be embedded in the wafer **290**.

Accordingly, the second incident light beam IR.sub.incident has to have power sufficient to pass through the entire thickness of the wafer **290** in order to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. In an embodiment, the second pattern **302** can be formed on a front side of a carrier wafer before the front side of the carrier wafer is bonded to a back side of a target wafer (e.g., the back side **392** of the wafer **290**). As a result, the second pattern **302** can be sandwiched between the carrier wafer and the target wafer, which together function as one wafer. Accordingly, the second incident light beam IR.sub.incident has to have power sufficient to pass through the entire thickness of the target wafer in order to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. In some embodiments, light projection can also be used. For example, the second pattern **302** can be a projected grid that does not physically exist in the wafer **290**, on a substrate holder or as a grid plate under the substrate holder. In some embodiments, the second pattern **302** may be a combination of physical marks and light projection. For example, physical reference marks may be provided on a peripheral region of a substrate holder that is not covered by a wafer placed on the substrate holder, and light projections can complete the reference pattern in the area of the wafer such that tunneling may not be necessary.

(36) FIG. 4A shows an enlarged top view of superimposed images of a portion of the wafer **290** captured by the first image capturing device **250** and the second image capturing device **260**, the portion including the first pattern **301** and the second pattern **302**, in accordance with some embodiments of the present disclosure. FIG. 4B demonstrates exemplary image analysis for overlay calculation using the first pattern **301**, which acts as a reference pattern in an alignment process, in accordance with some embodiments of the present disclosure. FIGS. 4A and 4B show how the absolute, independent first pattern **301** can be used to calculate an overlay value of two patterns. This can be done by knowing each common reference pattern to a co-ordinate system and using that reference pattern to know “where” each pattern is in that co-ordinate system. Once that is known, for example the distance between each layer, the vector calculation required to extract the overlay value is done with simple vector algebra. From that point, it is basic co-ordinate geometry. One can think of it as mix-match overlay (MMO) with a golden tool always there for oneself under the stage.

(37) In an embodiment, the first pattern **301** (denoted by a point M), e.g., the corner of one of the squares of the grid plate with 20 micrometers by 20 micrometers squares, can be considered absolute or wafer-independent and used to calculate an overlay value between the second pattern **302** (denoted by a point N) and a third pattern **401** (denoted by a point P) that is formed subsequent to the formation of the second pattern **302**. By superimposing the second pattern **302** on the first pattern **301**, a coordinate difference or vector  custom character from the point M of the first pattern **301** to the point N of the second pattern **302** can be determined. Likewise, by superimposing the third pattern **401** on the first pattern **301**, another coordinate difference or vector  custom character from the point M of the first pattern **301** to the point P of the third pattern **401**

can also be determined. Then, an overlay value  can be calculated:  custom character =  custom character -  custom character

(38) Further, with coordinate locations of points (e.g., N(Wx, Wy)) from the second pattern **302** and coordinate locations of points (e.g., P(Bx, By)) from the third pattern **401**, an overlay value or shift from the second pattern **302** to the third pattern **401** can be determined. This overlay value can then be used to place the third or subsequent pattern to correct overlay relative to the independent reference pattern, e.g., the first pattern **301**. In some embodiments, having a reference image that is uniform for every image comparison enables correcting adjacent patterns as well as keeping overlay corrections based on an initial line or absolute reference. Regarding concerns about critical dimension (CD) variation effects for resist layers, techniques herein can extract coordinates of the patterns without pattern CD variation effects for a resist layer and an under-layer thereof (e.g., metal resist patterns cover most of via patterns). CD variation effects for resist layers can be an issue for alignment and be ignored by overlay measurement teams as negligible. Techniques herein are far improved as the reference pattern itself is a far better indication of pattern placement than an alignment mark that suffers from CD's astigmatism and Zernike induced offset from patterns. Note that in some embodiments, superimposing images is not necessary. Coordinate location data can be collected from the reference plate and the working surface of the wafer, and then vector analysis can be used to determine a gross offset or an overlay value.

(39) FIG. 5 is a flow chart illustrating an exemplary imaging method **500** for processing a wafer (e.g., the wafer **290**) in accordance with some embodiments of the present disclosure. The exemplary imaging method **500** can be applied to the exemplary imaging system **200**. In various embodiments, some of the steps of the exemplary imaging method **500** shown can be performed concurrently or in a different order than shown, can be substituted by other method steps, or can be omitted. Additional method steps can also be performed as desired.

(40) At step **S510**, a wafer can be imaged with a first light beam (e.g., the first incident light beam UV.sub.incident) and a second light beam (e.g., the second incident light beam IR.sub.incident) that is coaxially aligned with the first light beam. In an embodiment, the first light beam can image a first pattern located on a front side of the wafer to form a first image (e.g., by capturing the first reflection light beam UV.sub.reflection), and the second light beam can image a second pattern located below the first pattern to form a second image (e.g., by capturing the second reflection light beam IR.sub.reflection). For example, the second light beam can have power sufficient to pass through at least a portion of a thickness of the wafer and reach the second pattern. In an embodiment, the second light beam can have a second wavelength longer than a first wavelength of the first light beam. For example, the first light beam can be generated by the first light source **210** such as a UV light source, and the second light beam can be generated by the second light source **220** such as an IR light source. In an embodiment, the first wavelength is 50-400 nanometers, e.g., 266 nanometers, and the second wavelength is 1-10 micrometers, e.g., 3.6 or 3.7 micrometer. In an embodiment, the second pattern can be imaged via quantum tunneling imaging or IR transmission imaging

(41) In an embodiment, the second pattern can be incorporated in a reference plate, e.g., the grid plate with 20 micrometers by 20 micrometers squares with sub-nanometers positional accuracy, located below the wafer. For example, the reference plate can be placed or adhered to the back side of the wafer. Accordingly, the second light beam can have power sufficient to pass through the entire thickness of the wafer to capture the second image of the second pattern using quantum tunneling imaging, IR transmission imaging or the like. In another embodiment, the reference plate can be incorporated in a substrate holder or chuck of a photolithography scanner or stepper, and the exemplary imaging method **500** can further include a step of aligning the reference plate with the wafer, prior to imaging the wafer with the first light beam and the second light beam. In yet another embodiment, the second pattern can be formed on the back side of the wafer. Accordingly, the second light beam can have power sufficient to pass through the entire thickness of the wafer to

capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. In still another embodiment, the second pattern can be embedded within the wafer and accessible through one or more layers. Accordingly, the second light beam can have power sufficient to pass through a portion of the thickness of the wafer to capture the second image of the second pattern **302** using quantum tunneling imaging, IR transmission imaging or the like. For example, the second pattern can include a radioactive or fluorescent material. As another example, the second pattern can include at least one of a point, a line, a corner, a box, a triangle, a number and a mark.

(42) At step **520**, image analysis can be performed on the first image and the second image to calculate an overlay value of the first pattern and the second pattern. For example, the image analysis can be performed by identifying coordinate locations of the first pattern relative to the second pattern as the overlay value, as shown in FIGS. **4A** and **4B**.

(43) At step **S530**, the first pattern can thus be formed on the front side of the wafer based on the overlay value. For example, a photomask of the first pattern can be moved relative to the wafer based on the overlay value such that the first pattern is aligned with the second pattern, and a resist layer formed on the front side of the wafer can be exposed to allow the first pattern to be formed in the resist layer.

(44) In an embodiment, in a “step-and-repeat” or “step-and-scan” system the first and second light beams and the photo mask can be moved to another area of the wafer, and steps **S510-S530** can be repeated to form one or more patterns in the resist layer on the front side of the wafer.

(45) A reference pattern used for patterning herein can be considered as absolute in one way, and relative in another. For example, the reference pattern may keep or maintain fixed grid lines (or points or corners or boxes or any other suitable shapes) and is not changed from various deposition and etch steps on the wafer. In an embodiment, this can be a grid plate integrated with a stage or substrate holder. In this way the grid plate is absolute because the same physical grid plate is used throughout processing of the wafer, but relative because the physical grid plate is not fixed to the wafer itself and may be moved relative to the wafer throughout wafer processing. Although each time a given wafer is placed on the stage, it may be in a different location or orientation as compared to a previous placement; this does not matter. For a given new pattern to be placed or exposed, the wafer is imaged with the reference grid. The reference grid can then provide a relative reference point for identifying vectors to two or more points, from which vector analysis can be used to calculate an overlay correction adjustment in a next exposure.

(46) The exemplary imaging system **200** and the exemplary imaging method **500** can be implemented as standalone coaxial metrology system and method that can operate in combination with a lithography tool, integrated track coaxial metrology system and method with feed forward to linked lithography cells, or active coaxial metrology system and method that can be embedded in a lithography tool for real time correction.

(47) FIG. **6** is a functional block diagram of an exemplary inspection system **600** according to some embodiments of the present disclosure. The exemplary inspection system **600** can calculate an overlay value of a first pattern and a second pattern that are associated with a wafer and inspect defects of the wafer. For example, the exemplary inspection system **600** can include an imaging module **610**, e.g., the imaging system **200**, and processing circuitry **620**. In an embodiment, the imaging module **610** can image a wafer with a first light beam and a second light beam that is coaxially aligned with the first light beam, the first light beam imaging a first pattern located on a front side of a wafer to form a first image, the second light beam imaging a second pattern located below the first pattern to form a second image, the second light beam having power sufficient to pass through at least a portion of a thickness of the wafer and reach the second pattern. For example, the imaging module **610** can image the wafer **290** with the first light beam generated by the first light source **210**, e.g., a UV light source, and the second light beam generated by the second light source **220**, e.g., an IR light source such as IR tunable quantum cascade lasers, the first

light beam can image the first pattern **301** located on the front side **391** of the wafer **290**, and the second light beam can image the second pattern **302** located below the first pattern **301** and have power sufficient to pass through at least a portion of the thickness of the wafer **290** and reach the second pattern **302**. The processing circuitry **620** can perform image analysis on the first image of the first pattern **301** and the second image of the second pattern **302** to calculate an overlay value of the first pattern **301** and the second pattern **302**.

(48) Each wafer may have scratch impact, heat impact and chucking issues, etc., which are deep enough to impact overlay. The wafer may further have patterning defects, which may exist if lines are not connected as designed, critical dimensions are too small/too large, or there are gaps that would cause shorts. As the second light beam can pass through the wafer **290**, the second light beam can also see the defects, and the second image captured can further include the information of the defects. In an embodiment, the processing circuitry **620** can further inspect any defects of the wafer **290** by performing the image analysis on the first image of the first pattern **301** and the second image of the second pattern **302**.

(49) Aspects of the present disclosure provide an imaging method, which can provide an accurate and precise alignment mechanism that does not rely on conventional alignment marks formed on a front surface of a wafer. Instead, with reference to a pattern or grid within/below the wafer, a reliable reference pattern can be repeatedly accessed for precise and accurate registration and alignment of subsequent patterns. The techniques herein will wipe out the need for traditional overlay marks. These novel paradigms for overlay can require no clear outs, no loss in real-estate and no complex scribe line design, making silicon area utilization improved and no complex integrations for alignment marks. The exemplary reference pattern disclosed herein will not be impacted and wiped out by unfavorable processes that are making devices instead of the alignment marks, as they often are conventionally. Overlay placement accuracy can also now be measured from the very first layer where the second pattern is located, as the reference pattern is now not only near perfect every time but hidden right under the stage there always.

(50) In the preceding description, specific details have been set forth, such as a particular geometry of a processing system and descriptions of various components and processes used therein. It should be understood, however, that techniques herein may be practiced in other embodiments that depart from these specific details, and that such details are for purposes of explanation and not limitation. Embodiments disclosed herein have been described with reference to the accompanying drawings. Similarly, for purposes of explanation, specific numbers, materials, and configurations have been set forth in order to provide a thorough understanding. Nevertheless, embodiments may be practiced without such specific details. Components having substantially the same functional constructions are denoted by like reference characters, and thus any redundant descriptions may be omitted.

(51) Various techniques have been described as multiple discrete operations to assist in understanding the various embodiments. The order of description should not be construed as to imply that these operations are necessarily order dependent. Indeed, these operations need not be performed in the order of presentation. Operations described may be performed in a different order than the described embodiment. Various additional operations may be performed and/or described operations may be omitted in additional embodiments.

(52) “Substrate” or “target substrate” as used herein generically refers to an object being processed in accordance with the present disclosure. The substrate may include any material portion or structure of a device, particularly a semiconductor or other electronics device, and may, for example, be a base substrate structure, such as a semiconductor wafer, reticle, or a layer on or overlying a base substrate structure such as a thin film. Thus, substrate is not limited to any particular base structure, underlying layer or overlying layer, patterned or un-patterned, but rather, is contemplated to include any such layer or base structure, and any combination of layers and/or base structures. The description may reference particular types of substrates, but this is for

illustrative purposes only.

(53) Those skilled in the art will also understand that there can be many variations made to the operations of the techniques explained above while still achieving the same objectives of the present disclosure. Such variations are intended to be covered by the scope of this disclosure. As such, the foregoing descriptions of embodiments of the present disclosure are not intended to be limiting. Rather, any limitations to embodiments of the present disclosure are presented in the following claims.

Claims

1. An inspection system, comprising: an imaging module configured to image a wafer with a first light beam and a second light beam that is coaxially aligned with the first light beam, the first light beam imaging a first pattern located on a front side of a wafer to form a first image, the second light beam imaging a second pattern located below the first pattern to form a second image, the second light beam having power sufficient to pass through at least a portion of a thickness of the wafer and reach the second pattern; and processing circuitry configured to perform image analysis on the first image and the second image to calculate at least one of an overlay value of the first pattern and the second pattern and inspect defects of the wafer, wherein the first light beam has a first wavelength that is 266 nanometers, the second light beam has a second wavelength that is 3.6 or 3.7 micrometers, and the first light beam and the second light beam are generated by separate light sources.
2. The inspection system of claim 1, wherein the second pattern is formed on a back side of the wafer.
3. The inspection system of claim 1, wherein the second pattern includes a radioactive or fluorescent material.
4. The inspection system of claim 1, wherein the second pattern includes at least one of a point, a line, a corner, a box, a triangle, a number and a mark.
5. The inspection system of claim 1, wherein the second pattern is incorporated in a reference plate located below the wafer.
6. The inspection system of claim 5, wherein the reference plate is placed on or adhered to a back side of the wafer.
7. The inspection system of claim 5, wherein the reference plate is incorporated in a substrate holder of a photolithography scanner or stepper.
8. An inspection system, comprising: an imaging module configured to image a wafer with a first light beam and a second light beam that is coaxially aligned with the first light beam, the first light beam imaging a first pattern located on a front side of a wafer to form a first image, the second light beam imaging a second pattern incorporated in a reference plate located below the wafer to form a second image, the second light beam having power sufficient to pass through an entire thickness of the wafer and reach the second pattern, the wafer containing silicon; and processing circuitry configured to perform image analysis on the first image and the second image to calculate at least one of an overlay value of the first pattern and the second pattern and inspect defects of the wafer, wherein the reference plate is adhered to a back side of the wafer.
9. The inspection system of claim 8, wherein the second light beam has a second wavelength longer than a first wavelength of the first light beam.
10. The inspection system of claim 9, wherein the first wavelength is in a range of 50-400 nanometers, and the second wavelength is in a range of 1-10 micrometers.
11. The inspection system of claim 10, wherein the first wavelength is 266 nanometers, and the second wavelength is 3.6 or 3.7 micrometers.
12. The inspection system of claim 9, further comprising an ultraviolet (UV) light source configured to generate the first light beam, and an infrared (IR) light source configured to generate

the second light beam.

13. The inspection system of claim 8, wherein the second pattern is coaxially aligned with the wafer.

14. The inspection system of claim 8, wherein the processing circuitry performs the image analysis by identifying coordinate locations of the first pattern relative to the second pattern as the overlay value.
